

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor BCP68

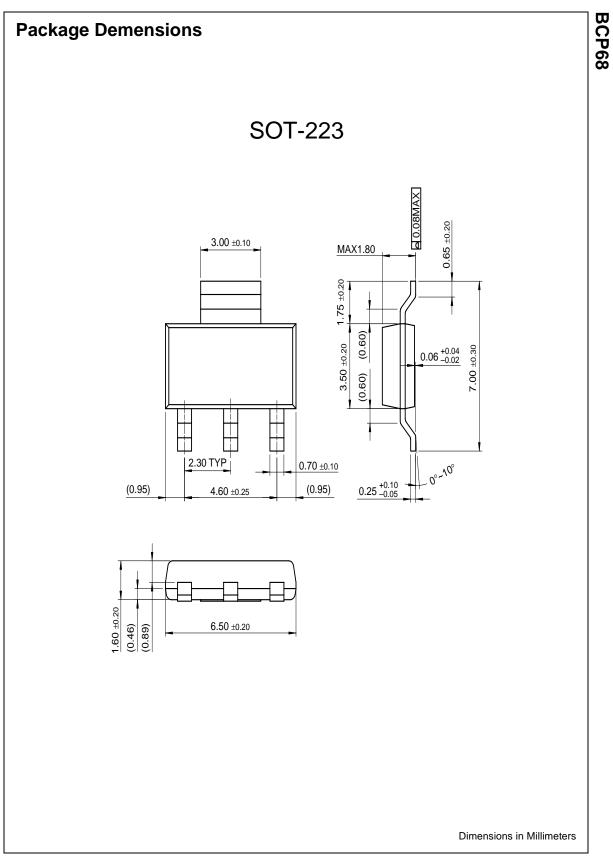
For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



	BCP68 NPN General Purpose Amplifier This device is designed for general purpose medium power amplifiers. Sourced from process 37.					4				
	² SOT-223 1. Base 2.4. Collector 3. Emitter									
bsolute	Maximum Ratings T _C =25°C un	less otherwise noted								
Symbol	Parameter			/alue)	ι	Inits			
V _{CEO}	Collector-Emitter Voltage			20			V			
V _{CBO}	Collector-Base Voltage			30			V			
V _{EBO}	Emitter-Base Voltage			5			V			
c	Collector Current			1			А			
P _D	Total Device Dissipation @ T - Derate above 25°C	_A =25°C		1.5 12			Vatts W/°C			
T _J , T _{STG}	Operating and Storage Junction Tem	perature Range	- 55	5 ~ +′	150	°C				
Electrical	Characteristics T _C =25°C unless	otherwise noted								
Symbol	Characteristics T _C =25°C unless Parameter ristics	otherwise noted Test Conditions	N	lin.	Тур.	Max.	Units			
Symbol	Parameter			lin. 25	Тур.	Max.	Units			
Symbol Off Characte	Parameter ristics	Test Conditions $I_C = 100\mu A$, $I_E = 0$ $I_C = 1mA$, $I_B = 0$			Тур.	Max.				
Symbol Off Characte V _{(BR)CES} V _{(BR)CEO}	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage	I _C = 100 μ A, I _E = 0 I _C = 1mA, I _B = 0 I _E = 10 μ A, I _C = 0		25	Тур.	Max.	V			
Symbol Off Characte V _{(BR)CES} V _{(BR)CEO} V _{(BR)EBO}	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage	I _C = 100 μ A, I _E = 0 I _C = 1mA, I _B = 0 I _E = 10 μ A, I _C = 0 V _{CB} = 25V, I _E = 0, T _A = 2	25°C	25 20	Тур.	Max.	V V			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO CBO	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage	I _C = 100 μ A, I _E = 0 I _C = 1mA, I _B = 0 I _E = 10 μ A, I _C = 0	25°C	25 20	Тур.	10	V V V μΑ			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO On Characte	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Base Cutoff Current Emitter-Base Cutoff Current ristics (1)	Test Conditions $I_C = 100\mu A, I_E = 0$ $I_C = 1mA, I_B = 0$ $I_E = 10\mu A, I_C = 0$ $V_{CB} = 25V, I_E = 0, T_A = 2$ $V_{CB} = 25V, I_E = 0, T_A = 1$ $V_{EB} = 5V, I_C = 0$	25°C	25 20	Тур.	10 1	V V V μA mA			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO IEBO On Characte	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Base Cutoff Current Emitter-Base Cutoff Current	$\begin{tabular}{ c c c c c } \hline Test Conditions \\ \hline I_C = 100 \mu A, I_E = 0 \\ \hline I_C = 1mA, I_B = 0 \\ \hline I_E = 10 \mu A, I_C = 0 \\ \hline V_{CB} = 25V, I_E = 0, T_A = 2 \\ \hline V_{CB} = 25V, I_E = 0, T_A = 1 \\ \hline V_{EB} = 5V, I_C = 0 \\ \hline \hline I_C = 5mA, V_{CE} = 10V \\ \hline I_C = 500mA, V_{CE} = 1V \\ \hline I_C = 1A, V_{CE} = 1V \\ \hline \hline I_C = 1A, V_{CE} = 1V \\ \hline \hline \hline I_C = 1A, V_{CE} = 1V \\ \hline $	25°C	25 20	Typ.	10 1	V V V μA mA			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO On Characte	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Base Cutoff Current Emitter-Base Cutoff Current ristics (1)	Test Conditions $I_C = 100\mu A, I_E = 0$ $I_C = 1mA, I_B = 0$ $I_E = 10\mu A, I_C = 0$ $V_{CB} = 25V, I_E = 0, T_A = 2$ $V_{CB} = 25V, I_E = 0, T_A = 1$ $V_{EB} = 5V, I_C = 0$ I_C = 5mA, V_{CE} = 10V $I_C = 500mA, V_{CE} = 1V$	25°C	25 20 5 50 35	Typ.	10 1 10	V V V μA mA			

BCP68





©2001 Fairchild Semiconductor Corporation

Rev. A, August 2001



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST [®]
Bottomless™	FASTr™
CoolFET™	FRFET™
CROSSVOLT™	GlobalOptoisolator™
DenseTrench™	GTO™
DOME™	HiSeC™
EcoSPARK™	ISOPLANAR™
E ² CMOS™	LittleFET™
EnSigna™	MicroFET™
FACT™	MicroPak™
FACT Quiet Series™	MICROWIRE™

OPTOLOGIC[™] OPTOPLANAR[™] PACMAN[™] POP[™] Power247[™] PowerTrench[®] QFET[™] QS[™] QT Optoelectronics[™] Quiet Series[™] SLIENT SWITCHER[®] SMART STARTTMVCXTMSTAR*POWERTMStealthTMSuperSOTTM-3SuperSOTTM-6SuperSOTTM-6SyncFETTMTruTranslationTMTinyLogicTMUHCTMUHCTMUltraFET®

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.